Transistors

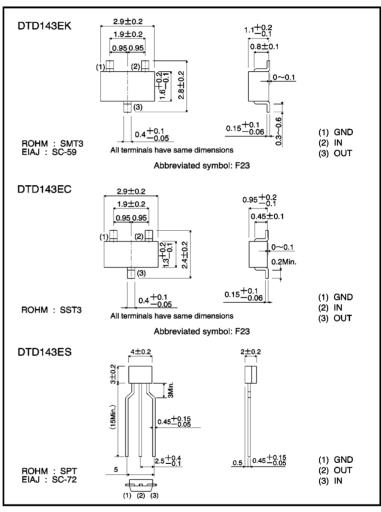
Digital transistors (built-in resistors) DTD143EK / DTD143ES / DTD143EC

Features

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- The bias resistors consist of thinfilm resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- Only the on/off conditions need to be set for operation, making device design easy.

Structure
NPN digital transistor
(Built-in resistor type)

External dimensions (Units: mm)

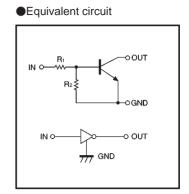




Transistors

•Absolute maximum ratings (Ta = 25° C)

Parameter	Symbol	Limit	Unit			
Falameter	Symbol	К	С	S	Unit	
Supply voltage	Vcc	50			V	
Input voltage	VIN	-10~+30			V	
Output current	lc	500			mA	
Power dissipation	Pd	200		300	mW	
Junction temperature	Tj	150			Ĉ	
Storage temperature	Tstg	-55~+150			Ĉ	



•Electrical characteristics (Ta = 25° C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Input voltage	VI(off)	_	_	0.5	v	Vcc=5V, Io=100 µ A	
	VI(on)	3	_	_		Vo=0.3V, Io=20mA	
Output voltage	VO(on)	_	0.1	0.3	V	lo/li=50mA/2.5mA	
Input current	h	_	_	1.8	mA	Vi=5V	
Output current	IO(off)	_	_	0.5	μA	Vcc=50V, Vi=0V	
DC current gain	Gi	47	_	_	_	Vo=5V, Io=50mA	
Input resistance	R1	3.29	4.7	6.11	kΩ		
Resistance ratio	R2/R1	0.8	1	1.2	_		
Transition frequency	fτ	_	200	_	MHz	Vce=10V, Ie=-50mA, f=100MHz *	

* Transition frequency of the device

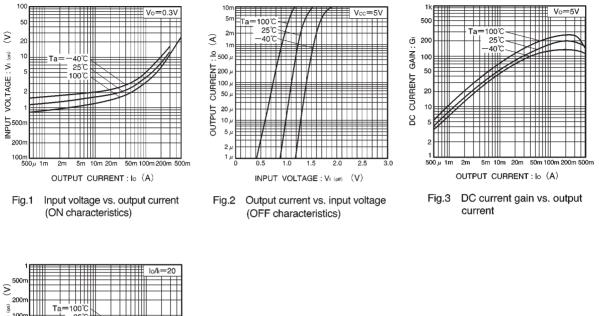
Packaging specifications

	Package	SMT3	SST3	SPT
	Packaging type	Taping	Taping	Taping
	Code	T146	T116	TP
Part No.	Basic ordering unit (pieces)	3000	3000	5000
DTD143EK		0	—	—
DTD143EC		—	—	0
DTD143ES		_	0	—

Transistors

DTD143EK / DTD143ES / DTD143EC

Electrical characteristic curves



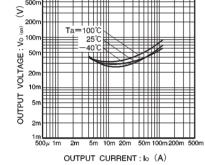


Fig.4 Output voltage vs. output current

